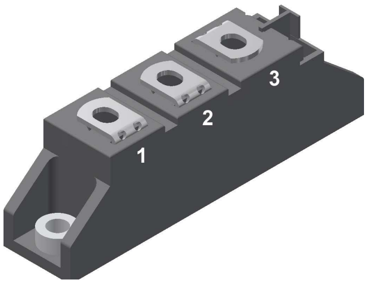
Standard Rectifier Module

V_{RRM} = 2x 1800 V
I_{FAV} = 59 A
V_F = 1.26 V

Phase leg

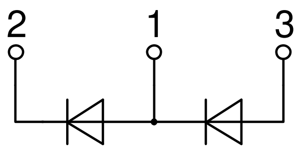
Part number

MDD44-18N1B



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

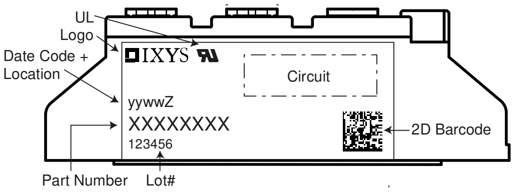
Disclaimer Notice

Rectifier

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1900	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1800	V
I_R	*reverse current*	V_R = 1800 V	T_{VJ} = 25°C			100	µA
		V_R = 1800 V	T_{VJ} = 150°C			10	mA
V_F	*forward voltage drop*	I_F = 100 A	T_{VJ} = 25°C			1.30	V
		I_F = 200 A				1.60	V
		I_F = 100 A	T_{VJ} = 125°C			1.26	V
		I_F = 200 A				1.67	V
I_{FAV}	*average forward current*	T_C = 100°C	T_{VJ} = 150°C			59	A
$I_{F(RMS)}$	*RMS forward current*	180° sine				100	A
V_{F0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.80	V
r_F	*slope resistance*					4.3	mΩ
R_{thJC}	*thermal resistance junction to case*					0.59	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.2		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			212	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.15	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.24	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			980	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.06	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			6.62	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			6.40	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			4.80	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			4.63	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		27		pF

Package TO-240AA

Symbol	Definition	Conditions			Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					200	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		125	°C
Weight						76		g
M_D	*mounting torque*				2.5		4	Nm
M_T	*terminal torque*				2.5		4	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	13.0	9.7			mm
$d_{Spb/Apb}$			*terminal to backside*	16.0	16.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \le 1$ mA		3600			V
		t = 1 minute			3000			V

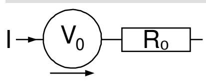


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD44-18N1B	MDD44-18N1B	Box	36	454397

Similar Part	Package	Voltage class
MDD44-08N1B	TO-240AA	800
MDD44-12N1B	TO-240AA	1200
MDD44-14N1B	TO-240AA	1400
MDD44-16N1B	TO-240AA	1600

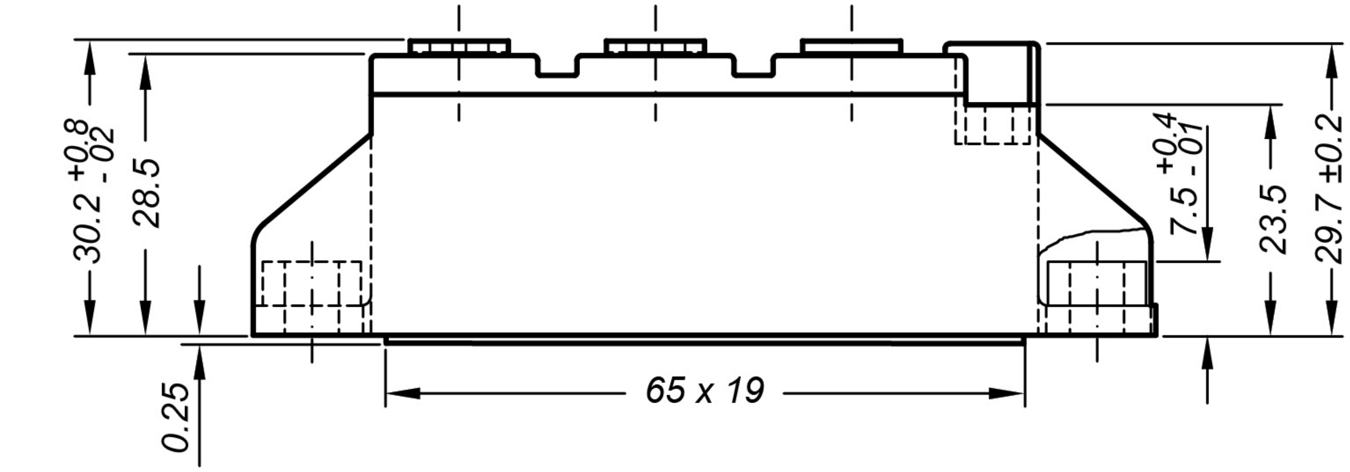
Equivalent Circuits for Simulation

** on die level* $T_{VJ} = 150°C$

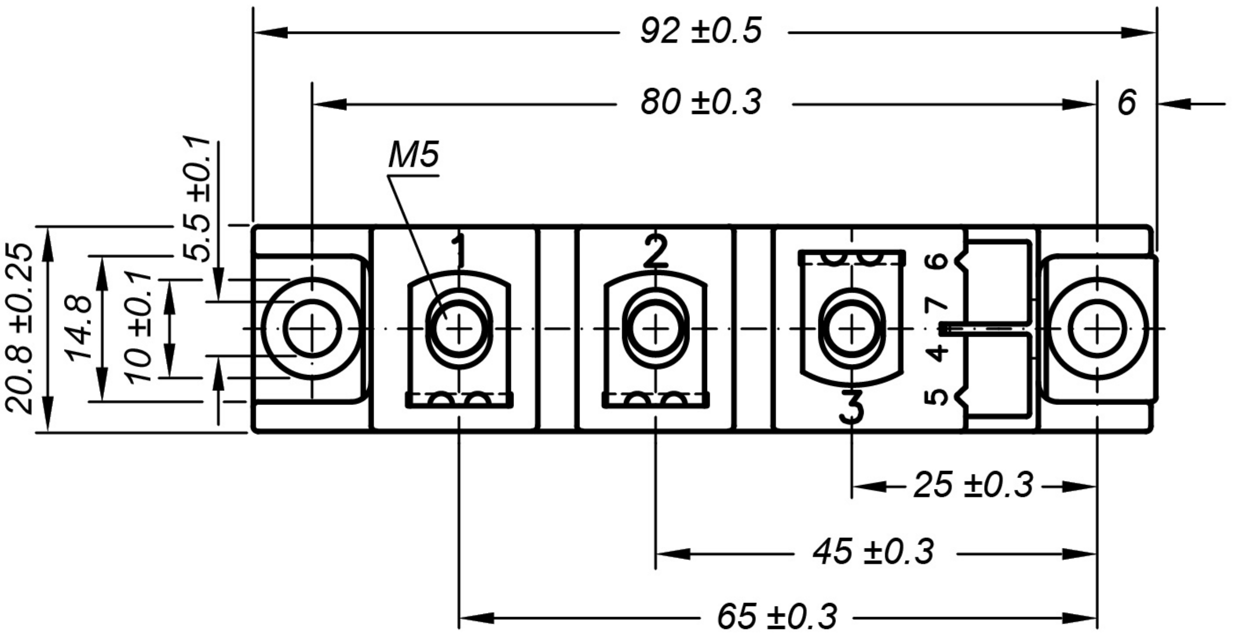


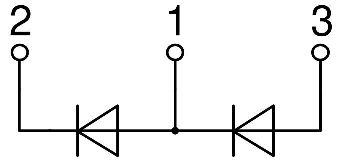
		Rectifier	
$V_{0\,max}$	*threshold voltage*	0.8	V
$R_{0\,max}$	*slope resistance **	3.1	mΩ

Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“





Rectifier

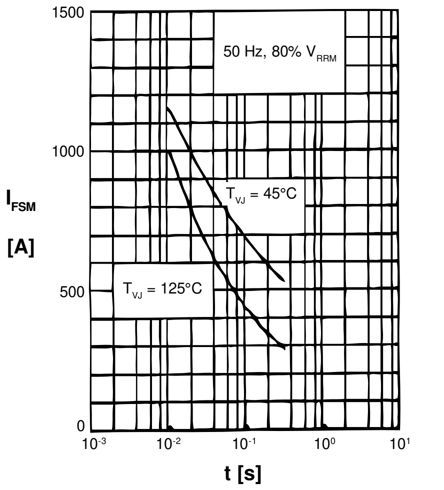


Fig. 1 Surge overload current
I_{TSM}, I_{FSM}: Crest value, t: duration

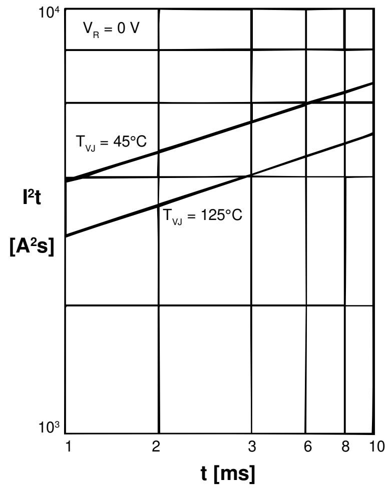


Fig. 2 I^2t versus time (1-10 ms)

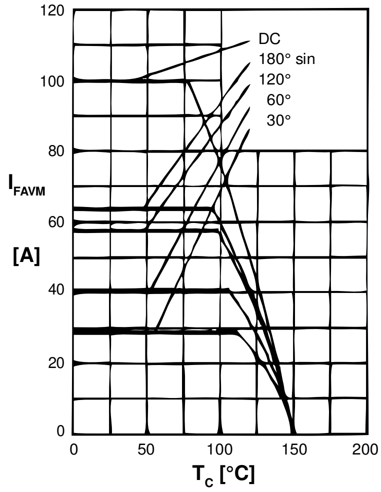


Fig. 3 Maximum forward current at case temperature

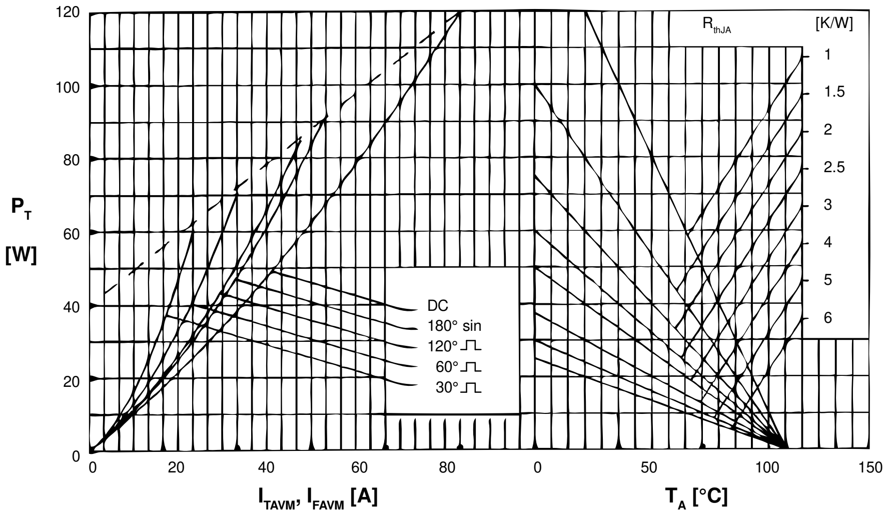


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per diode)

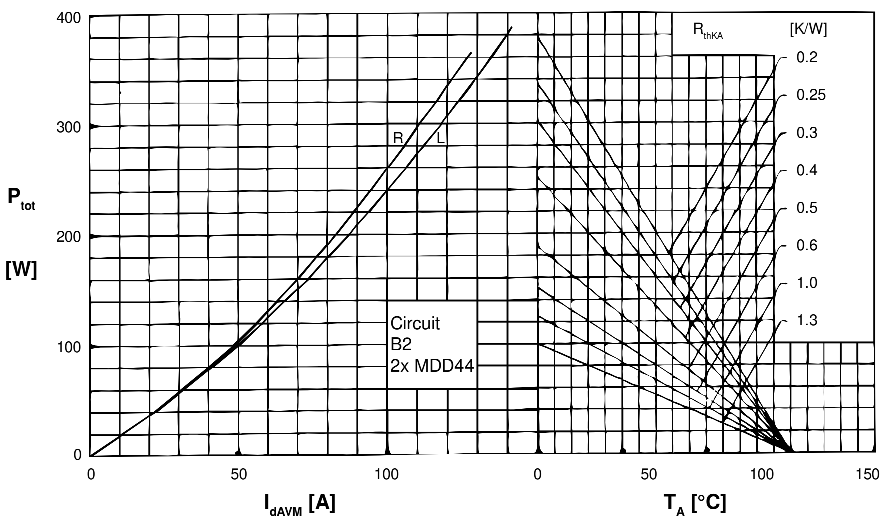


Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load

Rectifier

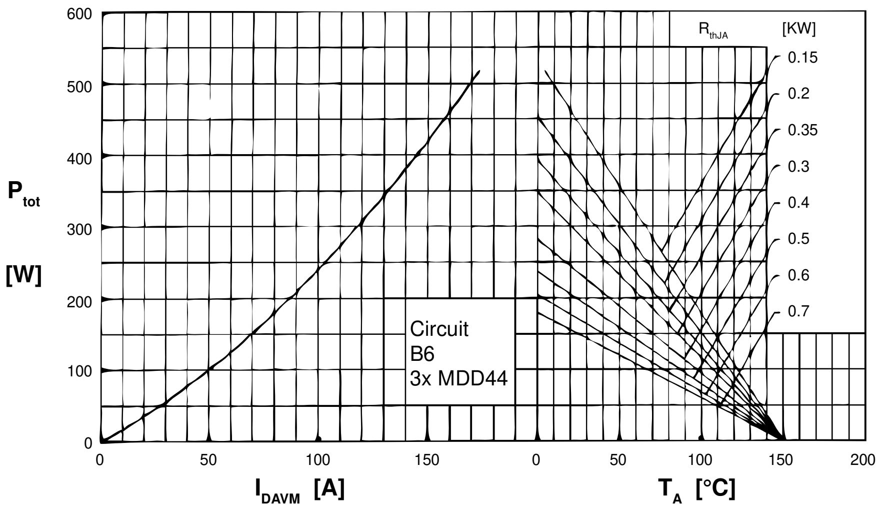


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

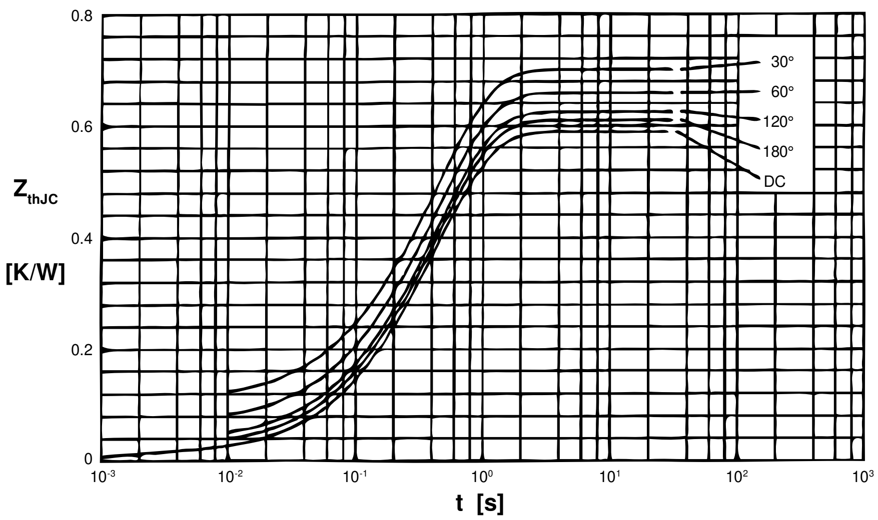


Fig. 7 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.59
180°	0.61
120°	0.63
60°	0.66
30°	0.70

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.012	0.0012
2	0.045	0.0950
3	0.533	0.4550

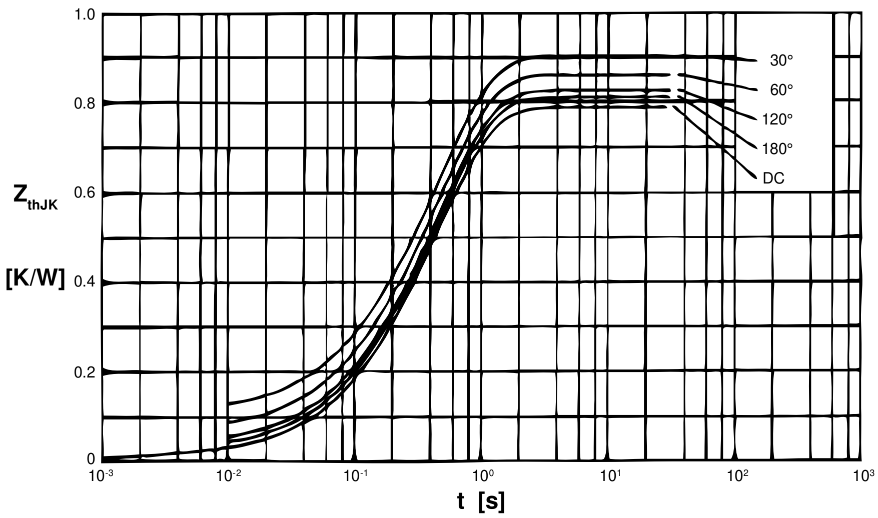


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.79
180°	0.81
120°	0.83
60°	0.86
30°	0.90

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.012	0.0012
2	0.045	0.0950
3	0.533	0.4550
4	0.200	0.4950